IPD068N10N3G-VB Datasheet

N-Channel 100V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
100	0.005 at V_{GS} = 10 V	100[a]

FEATURES

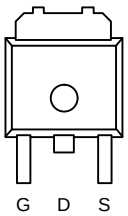
- Trench Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- 100 % R_g Tested

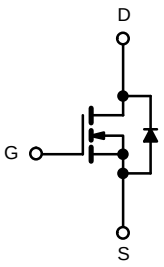
RoHS COMPLIANT

APPLICATIONS

- Isolated DC/DC Converters

TO-252





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)	T_C = 25 °C	I_D	100[a]	A
	T_C = 125 °C		80	
Pulsed Drain Current		I_{DM}	300	
Avalanche Current	L = 0.1 mH	I_{AS}	91	
Single Pulse Avalanche Energy[b]		E_{AS}	60	mJ
Maximum Power Dissipation[b]	T_C = 25 °C	P_D	155[c]	W
	T_A = 25 °C[d]		3.35	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		**Symbol**	**Limit**	**Unit**
Junction-to-Ambient	PCB Mount (TO-263)[d]	R_{thJA}	40	°C/W
Junction-to-Case (Drain)		R_{thJC}	0.4	

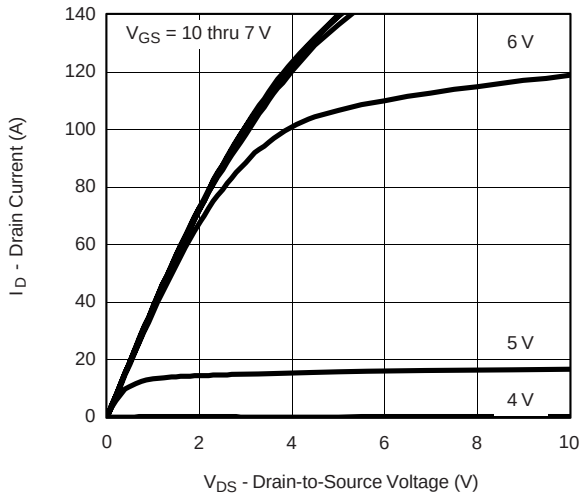
Notes:
a. Package limited.
b. Duty cycle ≤ 1 %.
c. See SOA curve for voltage derating.
d. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{DS} = 0 V, I_D = 250 µA	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2		4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	µA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 125 °C			50	
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 175 °C			250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	100			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.005		Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125 °C		0.008		
		V_{GS} = 10 V, I_D = 30 A, T_J = 175 °C		0.017		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	25			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2800		pF
Output Capacitance	C_{oss}			410		
Reverse Transfer Capacitance	C_{rss}			210		
Total Gate Charge[c]	Q_g	V_{DS} = 100 V, V_{GS} = 10 V, I_D = 58 A		90	130	nC
Gate-Source Charge[c]	Q_{gs}			23		
Gate-Drain Charge[c]	Q_{gd}			34		
Gate Resistance	R_g		0.5	1.3	3.1	Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 100 V, R_L = 1.5 Ω I_D ≅ 58 A, V_{GEN} = 10 V, R_g = 2.5 Ω		24	35	ns
Rise Time[c]	t_r			220	330	
Turn-Off Delay Time[c]	$t_{d(off)}$			45	70	
Fall Time[c]	t_f			200	300	
Source-Drain Diode Ratings and Characteristics T_C = 25 °C[b]						
Continuous Current	I_S				58	A
Pulsed Current	I_{SM}				110	
Forward Voltage[a]	V_{SD}	I_F = 58 A, V_{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t_{rr}	I_F = 30 A, di/dt = 100 A/µs		130	200	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			8	12	A
Reverse Recovery Charge	Q_{rr}			0.52	1.2	µC

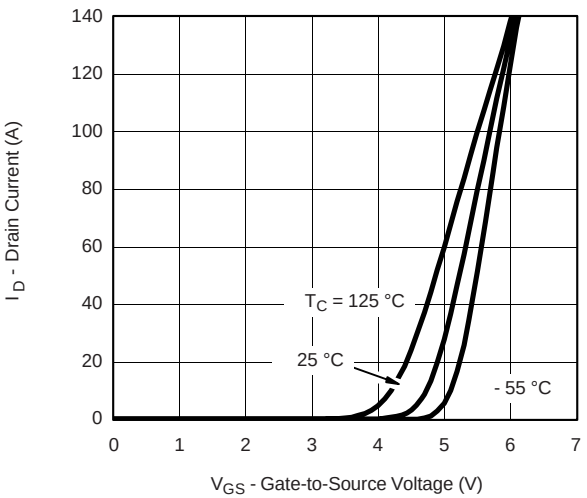
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

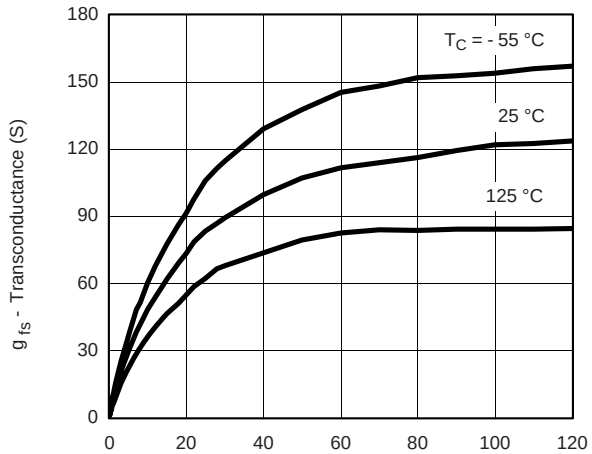
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



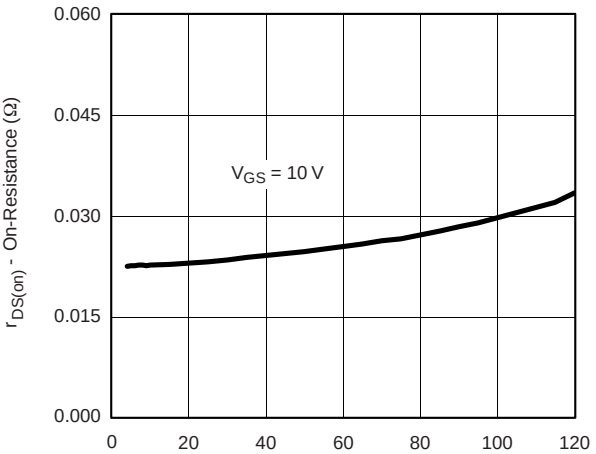
Output Characteristics



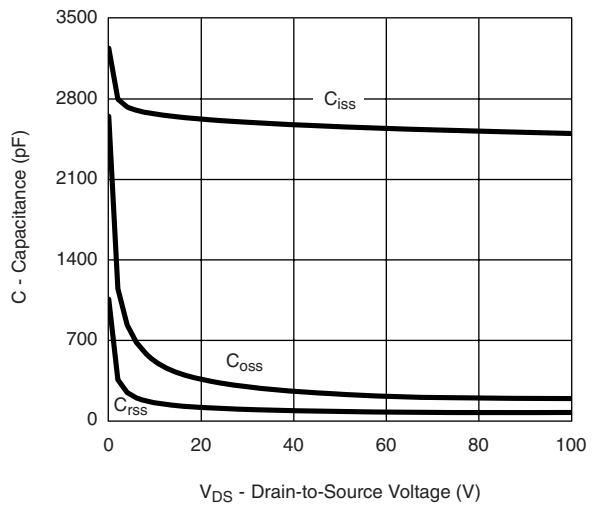
Transfer Characteristics



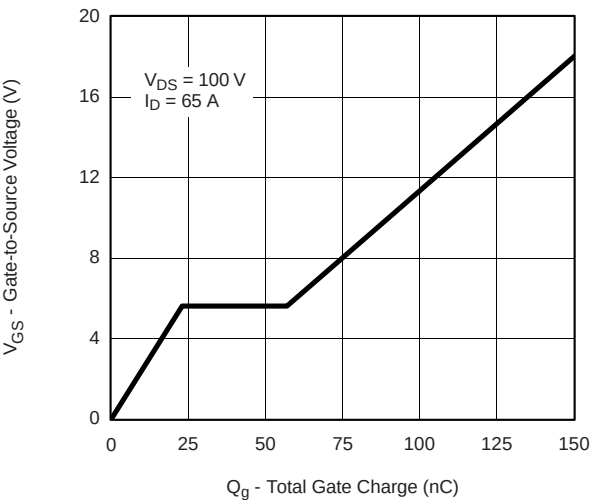
Transconductance



On-Resistance vs. Drain Current

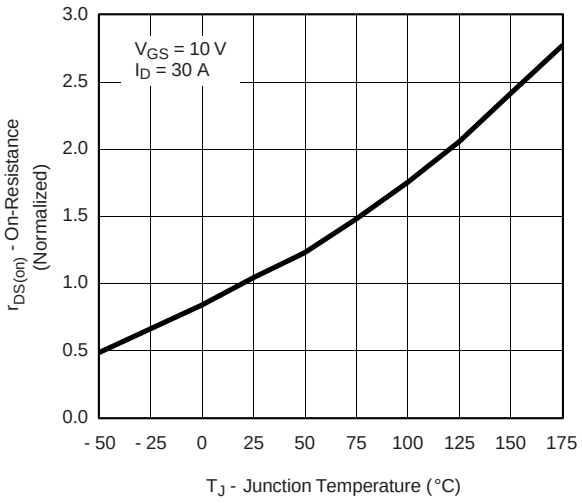


Capacitance

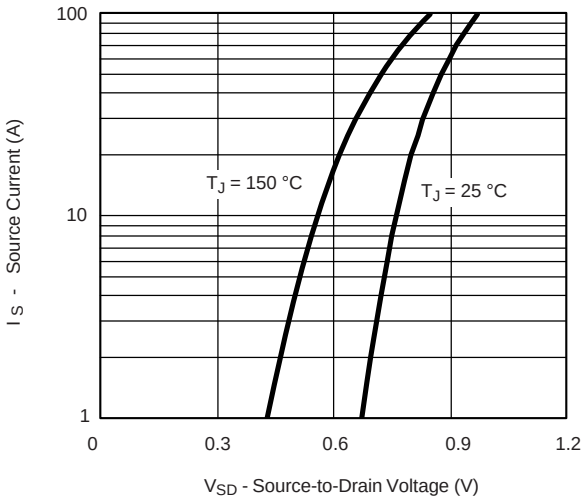


Gate Charge

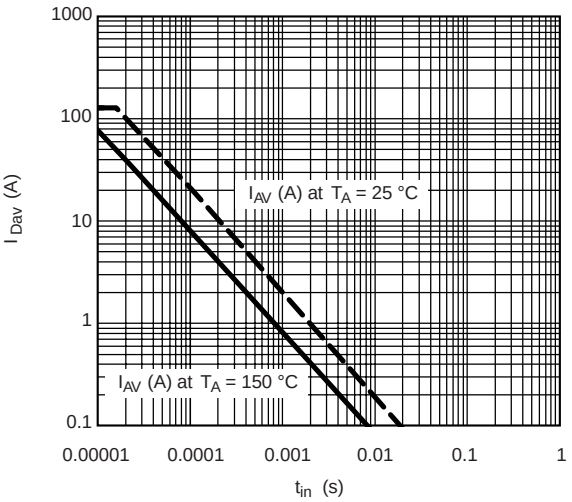
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



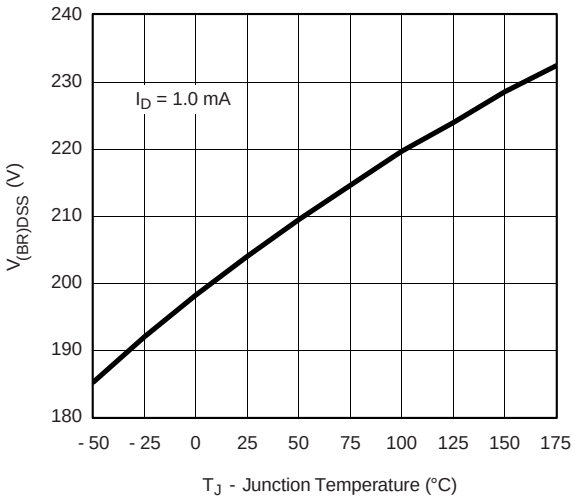
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

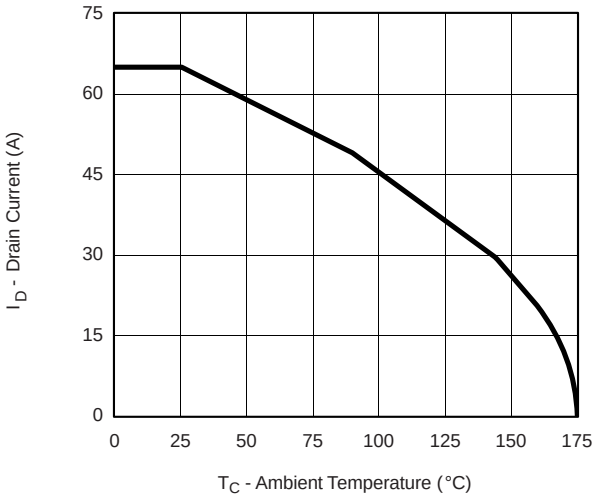


Avalanche Current vs. Time

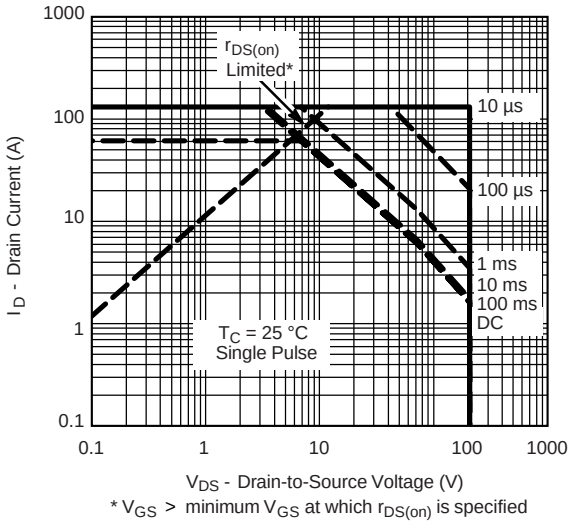


Drain Source Breakdown vs. Junction Temperature

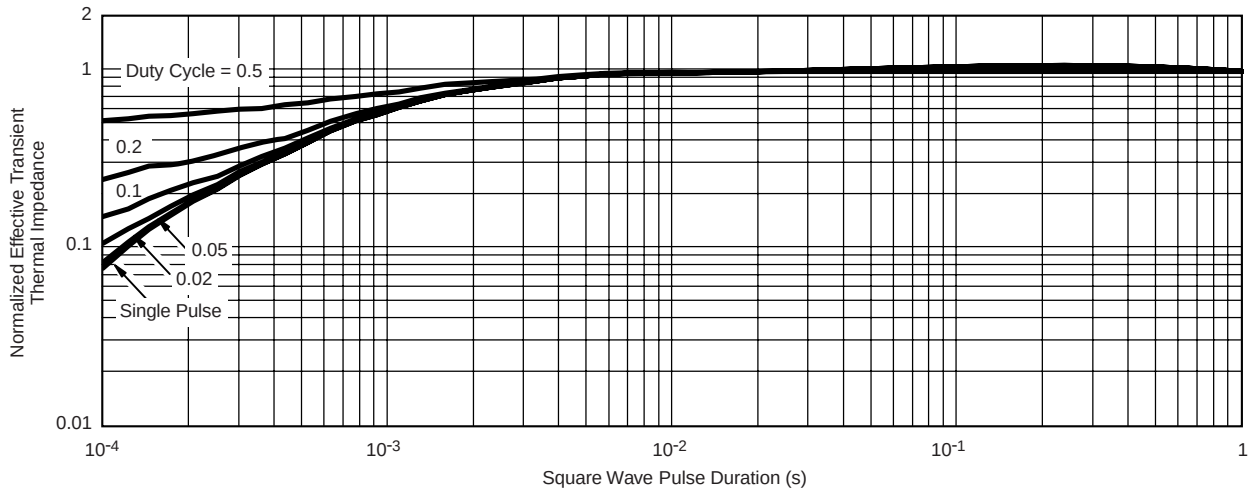
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature

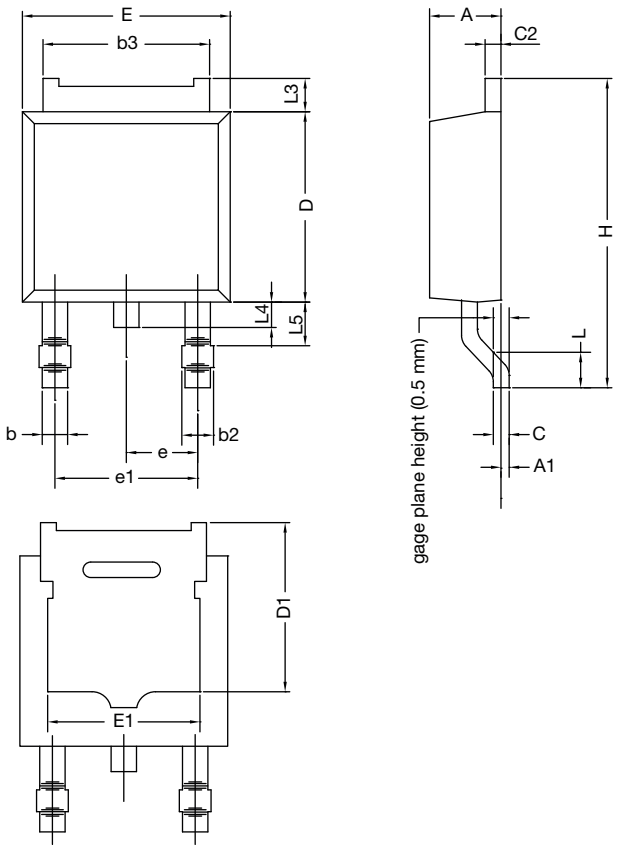


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE

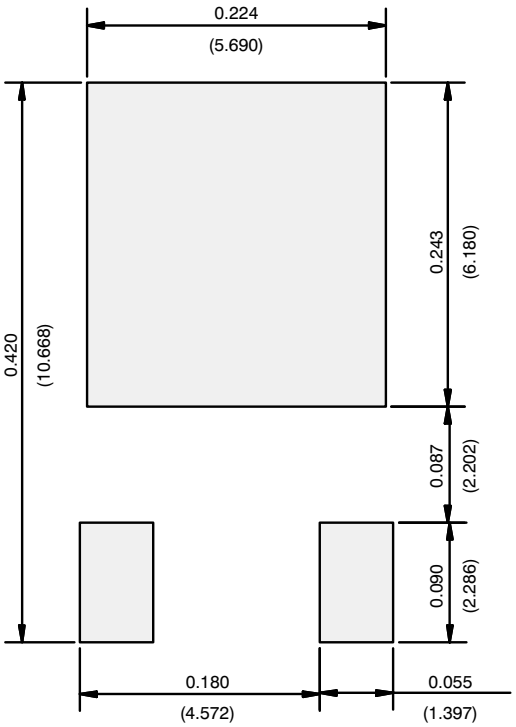


	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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